

IN THE CLAIMS

Please cancel claims 1-20 without prejudice or disclaimer thereof.

Listing of Claims

1-20 (canceled).

21. (New) A semiconductor integrated circuit device having a fuse portion for cutting off electrically using laser beam irradiation, said device comprising:

an insulating film formed on a semiconductor substrate,
a metal wiring layer formed on said insulating film to provide said fuse portion, wherein said metal wiring layer comprises at least a barrier metal layer formed on said insulating film and a main conducting metal layer formed on said barrier metal layer.

22. (New) A semiconductor integrated circuit device according to claim 21, wherein said barrier metal layer comprises one of (i) a single film such as a titanium nitride (TiN) film, a titanium (Ti) film and a tungsten nitride (WN) film and (ii) a multi-layered film consisting of a combination of above films.

23. (New) A semiconductor integrated circuit device according to

claim 21, wherein said barrier metal layer has a thickness of 150 nm or less.

24. (New) A semiconductor integrated circuit device according to claim 22, wherein said barrier metal layer has a thickness of 150 nm or less.

25. (New) A semiconductor integrated circuit device according to claim 21, wherein said main conducting metal layer is made of a metal primarily consisting of aluminum.

26. (New) A semiconductor integrated circuit device according to claim 22, wherein said main conducting metal layer is made of a metal primarily consisting of aluminum.

27. (New) A semiconductor integrated circuit device according to claim 23, wherein said main conducting metal layer is made of a metal primarily consisting of aluminum.

28. (New) A semiconductor integrated circuit device according to claim 24, wherein said main conducting metal layer is made of a metal primarily consisting of aluminum.

29. (New) A semiconductor integrated circuit device according to claim 21, wherein said metal wiring layer of said fuse portion is further provided with an antireflection film formed on said main conducting metal layer.

30. (New) A semiconductor integrated circuit device according to claim 21, wherein said semiconductor integrated circuit device comprises a plurality of metal wiring layers; and said metal wiring layer of said fuse portion is an uppermost metal wiring layer among the plurality of metal wiring layers.

31. (New) A semiconductor integrated circuit device according to any one of claim 21 to 30, wherein a wiring width of said fuse, portion where cutting off is to be performed is not smaller than 0.1 μm and not larger than 1.0 μm .